

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	10 A
V_{RRM}	45 V
V_F (max)	0.57 V

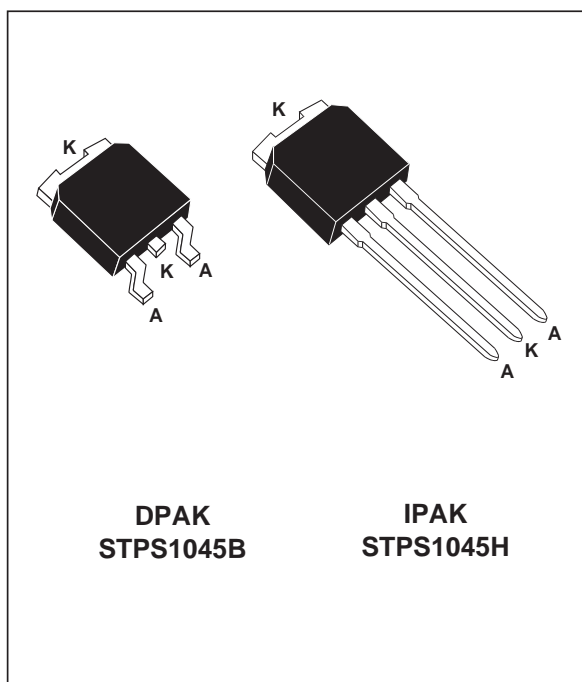
FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD DROP VOLTAGE
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY

DESCRIPTION

High voltage Schottky rectifier suited for Switch Mode Power Supplies and other Power Converters.

Packaged in DPAK and IPAK, these devices are intended for use in high frequency circuitries where low switching losses are required.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		45	V
$I_{F(RMS)}$ / pin	RMS forward current / pin		7	A
$I_{F(AV)}$	Average forward current	$T_c = 150^\circ\text{C}$ $d = 0.5$	10	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10$ ms Sinusoidal	75	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2$ μs $F = 1$ KHz	1	A
T_{stg}	Storage temperature range		- 65 to + 175	$^\circ\text{C}$
T_j	Maximum junction temperature		175	$^\circ\text{C}$
dV/dt	Critical rate of rise of reverse voltage		10000	V/ μs

STPS1045B/H

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	3	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit	
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = 45\text{ V}$			100	μA
		$T_j = 125^\circ\text{C}$			7	15	mA
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 10\text{ A}$			0.63	V
		$T_j = 125^\circ\text{C}$	$I_F = 10\text{ A}$		0.5	0.57	
		$T_j = 25^\circ\text{C}$	$I_F = 20\text{ A}$			0.84	
		$T_j = 125^\circ\text{C}$	$I_F = 20\text{ A}$		0.65	0.72	

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$
 ** $t_p = 5\ \text{ms}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :
 $P = 0.42 \times I_{F(AV)} + 0.015 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current.

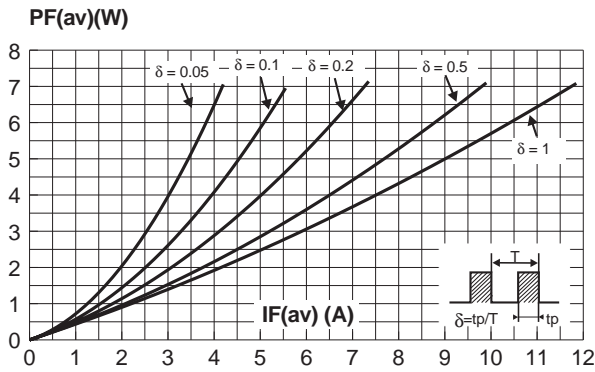


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values).

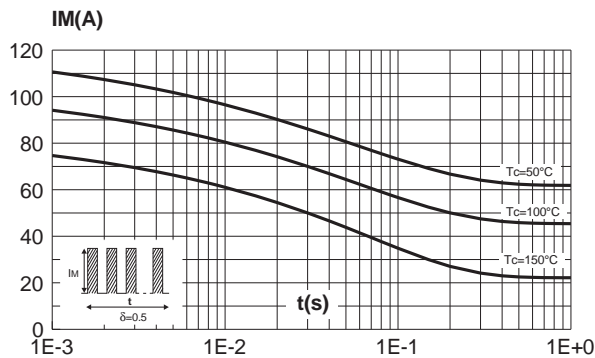


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

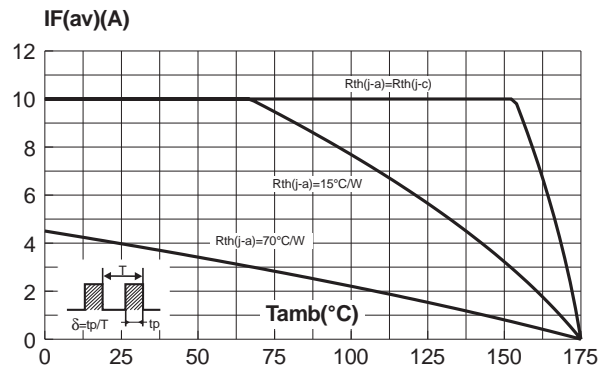


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration.

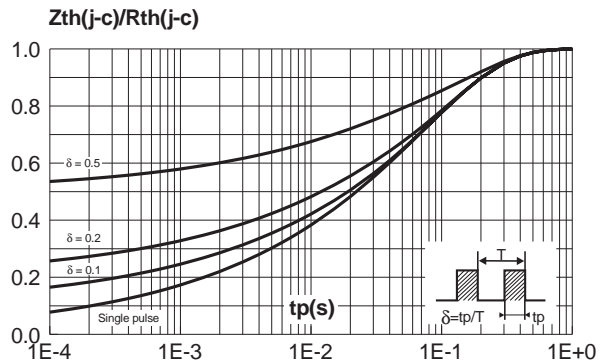


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values).

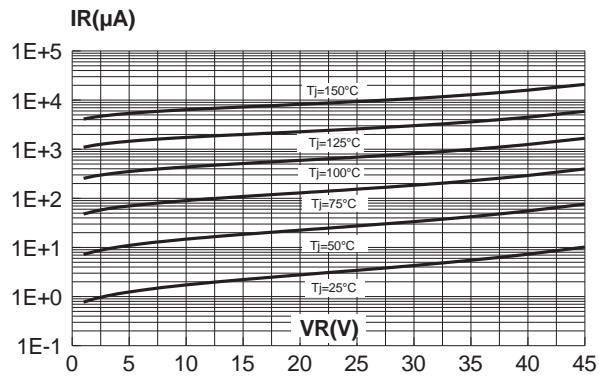


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

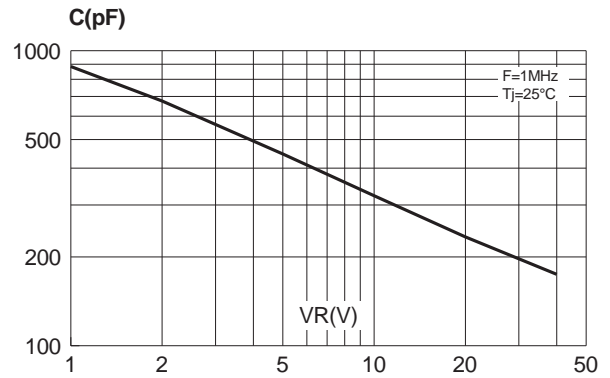


Fig. 7: Forward voltage drop versus forward current (maximum values).

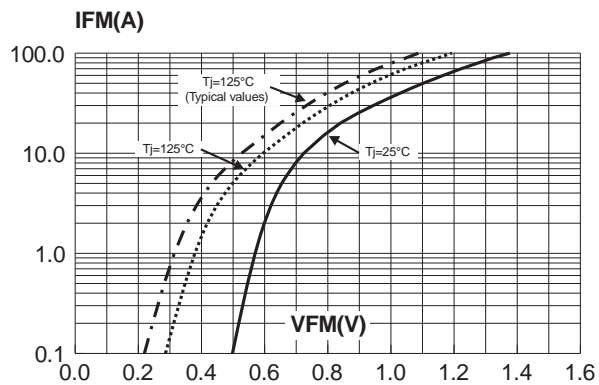
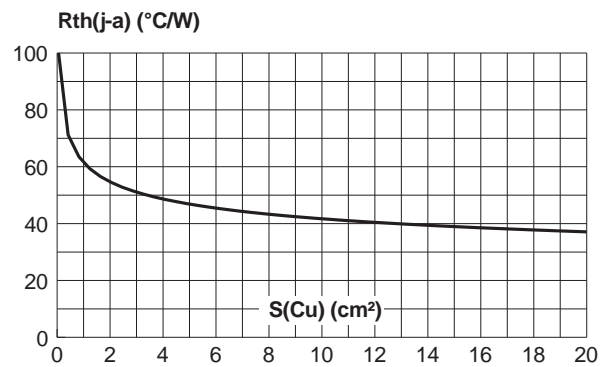
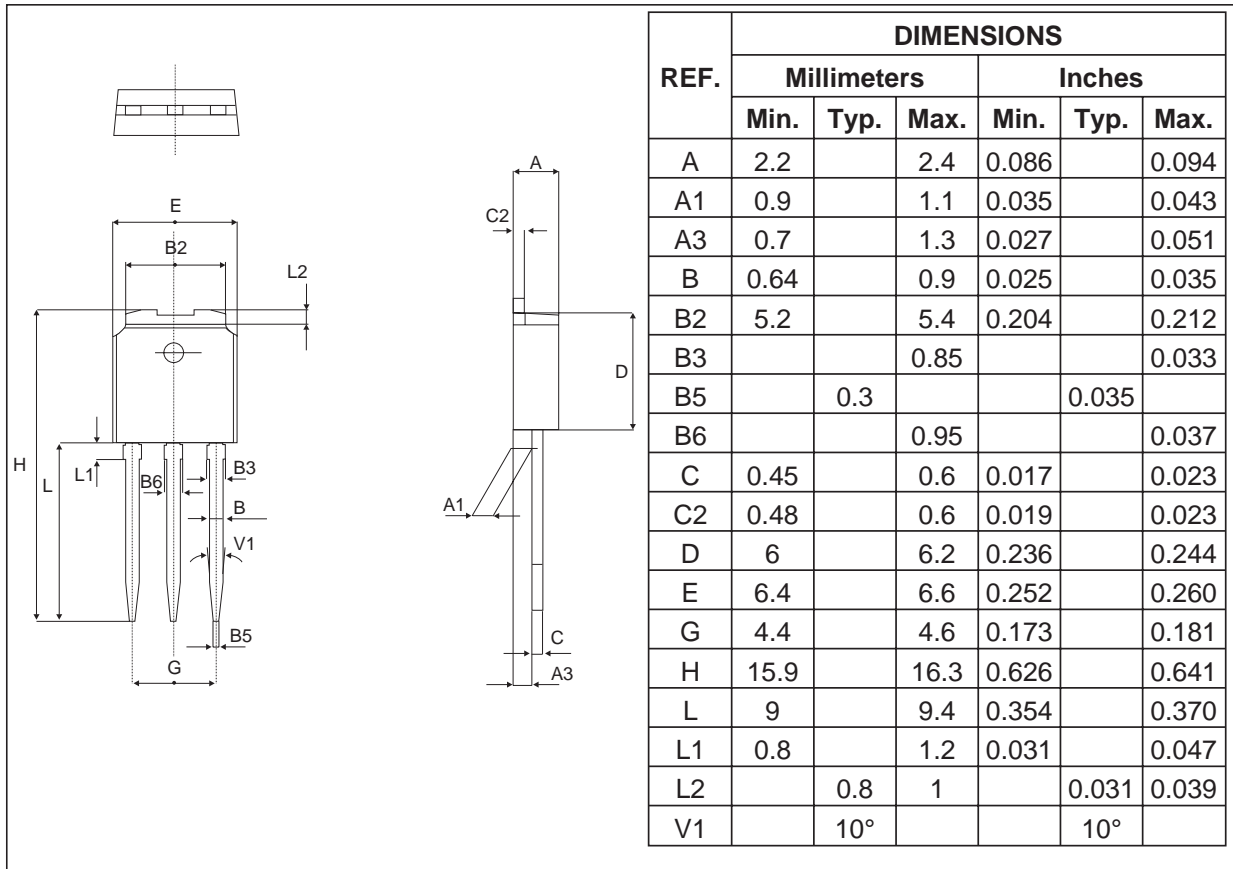


Fig. 8: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board, copper thickness: $35\mu\text{m}$) (STPS1045B).



STPS1045B/H

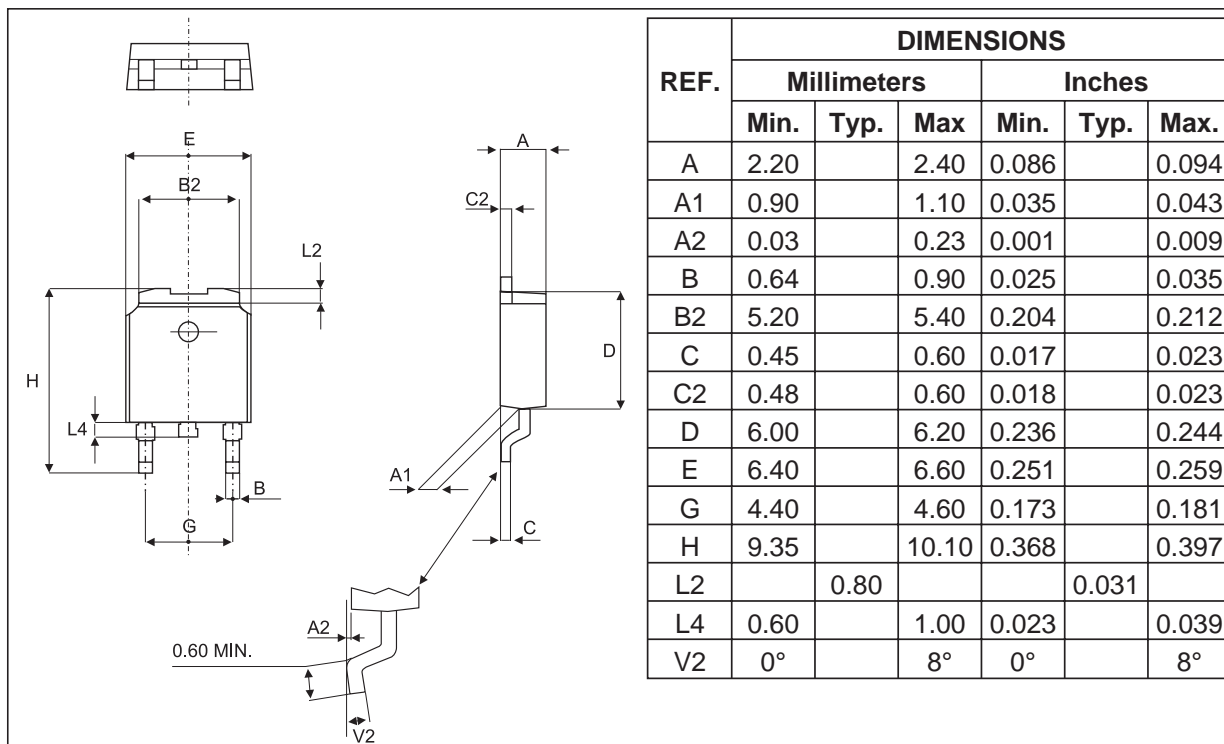
PACKAGE MECHANICAL DATA IPAK



- Cooling method: by conduction (C)

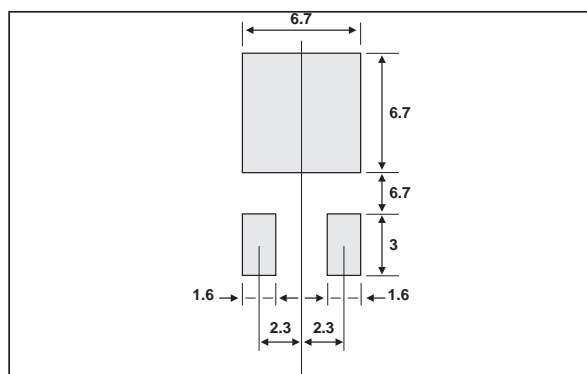
PACKAGE MECHANICAL DATA

DPAK



- Cooling method: by conduction (C)

FOOT PRINT DIMENSIONS (in millimeters)



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